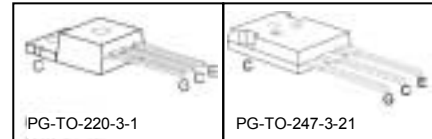
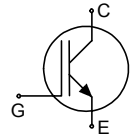


High Speed IGBT in NPT-technology

- 30% lower E_{off} compared to previous generation
- Short circuit withstand time – 10 μ s
- Designed for operation above 30 kHz
- NPT-Technology for 600V applications offers:
 - parallel switching capability
 - moderate E_{off} increase with temperature
 - very tight parameter distribution
- High ruggedness, temperature stable behaviour
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC¹ for target applications
- Complete product spectrum and PSpice Models : <http://www.infineon.com/igbt/>



| Type | V_{CE} | I_C | E_{off} | T_j | Marking | Package |
|------------|----------|-------|-------------|-------|----------|----------------|
| SGP30N60HS | 600V | 30 | 480 μ J | 150°C | G30N60HS | PG-TO-220-3-1 |
| SGW30N60HS | 600V | 30 | 480 μ J | 150°C | G30N60HS | PG-TO-247-3-21 |

Maximum Ratings

| Parameter | Symbol | Value | Unit |
|---|----------------|----------------------|------------------|
| Collector-emitter voltage | V_{CE} | 600 | V |
| DC collector current | I_C | | A |
| $T_C = 25^\circ\text{C}$ | | 41 | |
| $T_C = 100^\circ\text{C}$ | | 30 | |
| Pulsed collector current, t_p limited by T_{jmax} | I_{Cpuls} | 112 | |
| Turn off safe operating area | - | 112 | |
| $V_{CE} \leq 600\text{V}, T_j \leq 150^\circ\text{C}$ | | | |
| Avalanche energy single pulse $I_C = 20\text{A}, V_{CC} = 50\text{V}, R_{GE} = 25\Omega$ start $T_j = 25^\circ\text{C}$ | E_{AS} | 165 | mJ |
| Gate-emitter voltage static transient ($t_p < 1\mu\text{s}, D < 0.05$) | V_{GE} | ± 20 ± 30 | V |
| Short circuit withstand time ²⁾ $V_{GE} = 15\text{V}, V_{CC} \leq 600\text{V}, T_j \leq 150^\circ\text{C}$ | t_{SC} | 10 | μs |
| Power dissipation $T_C = 25^\circ\text{C}$ | P_{tot} | 250 | W |
| Operating junction and storage temperature | T_j, T_{stg} | -55...+150 | $^\circ\text{C}$ |
| Time limited operating junction temperature for $t < 150\text{h}$ | $T_{j(tl)}$ | 175 | |
| Soldering temperature, 1.6mm (0.063 in.) from case for 10s | - | 260 | |

¹ J-STD-020 and JESD-022

²⁾ Allowed number of short circuits: <1000; time between short circuits: >1s.

Thermal Resistance

| Parameter | Symbol | Conditions | Max. Value | Unit |
|--|------------|----------------|------------|------|
| Characteristic | | | | |
| IGBT thermal resistance, junction – case | R_{thJC} | | 0.5 | K/W |
| Thermal resistance, junction – ambient | R_{thJA} | PG-TO-220-3-1 | 62 | |
| | | PG-TO-247-3-21 | 40 | |

Electrical Characteristic, at $T_j = 25^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Value | | | Unit |
|--------------------------------------|---------------|---|-------|------|------|---------|
| | | | min. | Typ. | max. | |
| Static Characteristic | | | | | | |
| Collector-emitter breakdown voltage | $V_{(BR)CES}$ | $V_{GE}=0V, I_C=500\mu A$ | 600 | - | - | V |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $V_{GE} = 15V, I_C=30A$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$ | | 2.8 | 3.15 | |
| | | | | 3.5 | 4.00 | |
| Gate-emitter threshold voltage | $V_{GE(th)}$ | $I_C=700\mu A, V_{CE}=V_{GE}$ | 3 | 4 | 5 | |
| Zero gate voltage collector current | I_{CES} | $V_{CE}=600V, V_{GE}=0V$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$ | | - | 40 | μA |
| | | | | - | 3000 | |
| Gate-emitter leakage current | I_{GES} | $V_{CE}=0V, V_{GE}=20V$ | - | - | 100 | nA |
| Transconductance | g_{fs} | $V_{CE}=20V, I_C=30A$ | - | 20 | - | S |

Dynamic Characteristic

| | | | | | | |
|--|-------------|---|---|------|--|----|
| Input capacitance | C_{iss} | $V_{CE}=25V,$ $V_{GE}=0V,$ $f=1\text{MHz}$ | - | 1500 | | pF |
| Output capacitance | C_{oss} | | - | 150 | | |
| Reverse transfer capacitance | C_{riss} | | - | 92 | | |
| Gate charge | Q_{Gate} | $V_{CC}=480V, I_C=30A$ $V_{GE}=15V$ | - | 141 | | nC |
| Internal emitter inductance measured 5mm (0.197 in.) from case | L_E | PG-TO-220-3-1 | - | 7 | | nH |
| | | PG-TO-247-3-21 | | 13 | | |
| Short circuit collector current ¹⁾ | $I_{C(SC)}$ | $V_{GE}=15V, t_{SC}\leq 10\mu s$ $V_{CC}\leq 600V,$ $T_j\leq 150^\circ\text{C}$ | - | 220 | | A |

¹⁾ Allowed number of short circuits: <1000; time between short circuits: >1s.

Switching Characteristic, Inductive Load, at $T_j=25^\circ\text{C}$

| Parameter | Symbol | Conditions | Value | | | Unit |
|----------------------------|--------------|--|-------|------|------|------|
| | | | min. | typ. | max. | |
| IGBT Characteristic | | | | | | |
| Turn-on delay time | $t_{d(on)}$ | $T_j=25^\circ\text{C}$, $V_{CC}=400\text{V}$, $I_C=30\text{A}$, $V_{GE}=0/15\text{V}$, $R_G=11\Omega$ $L_{\sigma}^{(1)}=60\text{nH}$, $C_{\sigma}^{(1)}=40\text{pF}$ Energy losses include "tail" and diode reverse recovery. | - | 20 | | ns |
| Rise time | t_r | | - | 21 | | |
| Turn-off delay time | $t_{d(off)}$ | | - | 250 | | |
| Fall time | t_f | | - | 25 | | |
| Turn-on energy | E_{on} | | - | 0.60 | | mJ |
| Turn-off energy | E_{off} | | - | 0.55 | | |
| Total switching energy | E_{ts} | | - | 1.15 | | |

Switching Characteristic, Inductive Load, at $T_j=150^\circ\text{C}$

| Parameter | Symbol | Conditions | Value | | | Unit |
|----------------------------|--------------|--|-------|------|------|------|
| | | | min. | typ. | max. | |
| IGBT Characteristic | | | | | | |
| Turn-on delay time | $t_{d(on)}$ | $T_j=150^\circ\text{C}$ $V_{CC}=400\text{V}$, $I_C=30\text{A}$, $V_{GE}=0/15\text{V}$, $R_G=1.8\Omega$ $L_{\sigma}^{(1)}=60\text{nH}$, $C_{\sigma}^{(1)}=40\text{pF}$ Energy losses include "tail" and diode reverse recovery. | - | 16 | | ns |
| Rise time | t_r | | - | 13 | | |
| Turn-off delay time | $t_{d(off)}$ | | - | 122 | | |
| Fall time | t_f | | - | 29 | | |
| Turn-on energy | E_{on} | | - | 0.78 | | mJ |
| Turn-off energy | E_{off} | | - | 0.48 | | |
| Total switching energy | E_{ts} | | - | 1.26 | | |
| Turn-on delay time | $t_{d(on)}$ | $T_j=150^\circ\text{C}$ $V_{CC}=400\text{V}$, $I_C=30\text{A}$, $V_{GE}=0/15\text{V}$, $R_G=11\Omega$ $L_{\sigma}^{(1)}=60\text{nH}$, $C_{\sigma}^{(1)}=40\text{pF}$ Energy losses include "tail" and diode reverse recovery. | - | 20 | | ns |
| Rise time | t_r | | - | 19 | | |
| Turn-off delay time | $t_{d(off)}$ | | - | 274 | | |
| Fall time | t_f | | - | 27 | | |
| Turn-on energy | E_{on} | | - | 0.91 | | mJ |
| Turn-off energy | E_{off} | | - | 0.70 | | |
| Total switching energy | E_{ts} | | - | 1.61 | | |

¹⁾ Leakage inductance L_{σ} and Stray capacity C_{σ} due to test circuit in Figure E.

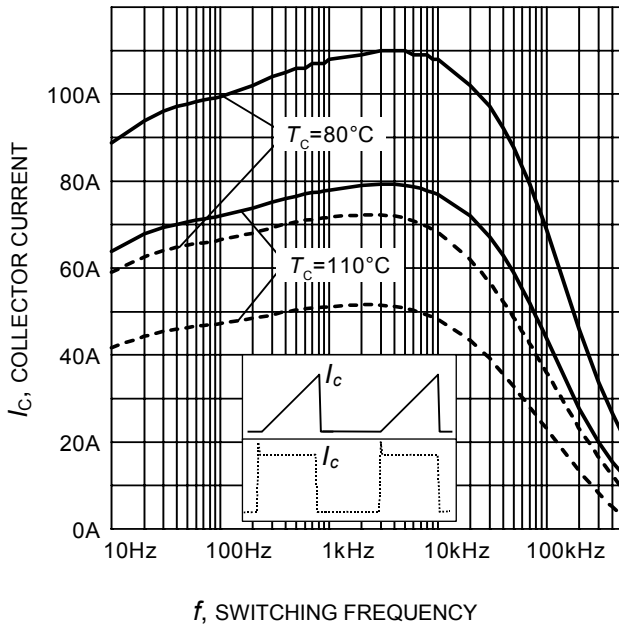


Figure 1. Collector current as a function of switching frequency
 ($T_j \leq 150^\circ\text{C}$, $D = 0.5$, $V_{CE} = 400\text{V}$,
 $V_{GE} = 0/+15\text{V}$, $R_G = 11\Omega$)

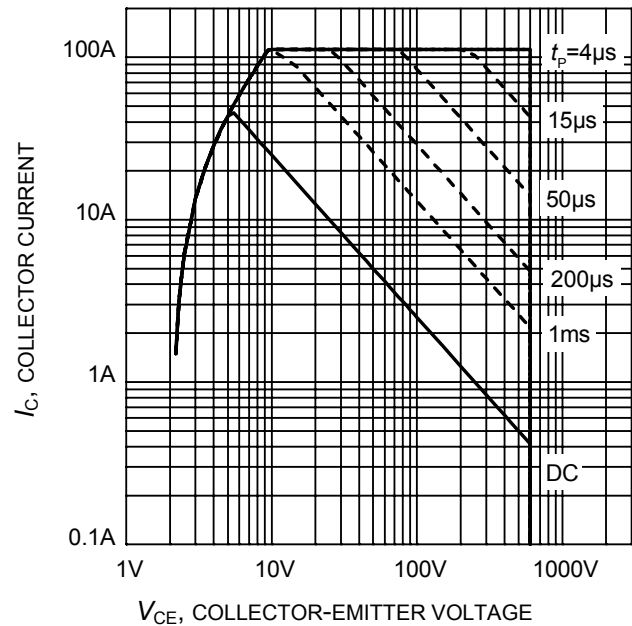


Figure 2. Safe operating area
 ($D = 0$, $T_C = 25^\circ\text{C}$, $T_j \leq 150^\circ\text{C}$;
 $V_{GE} = 15\text{V}$)

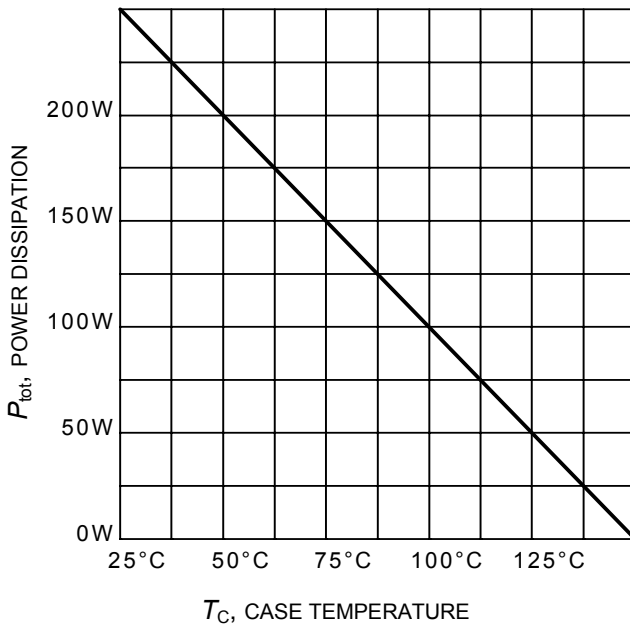


Figure 3. Power dissipation as a function of case temperature
 ($T_j \leq 150^\circ\text{C}$)

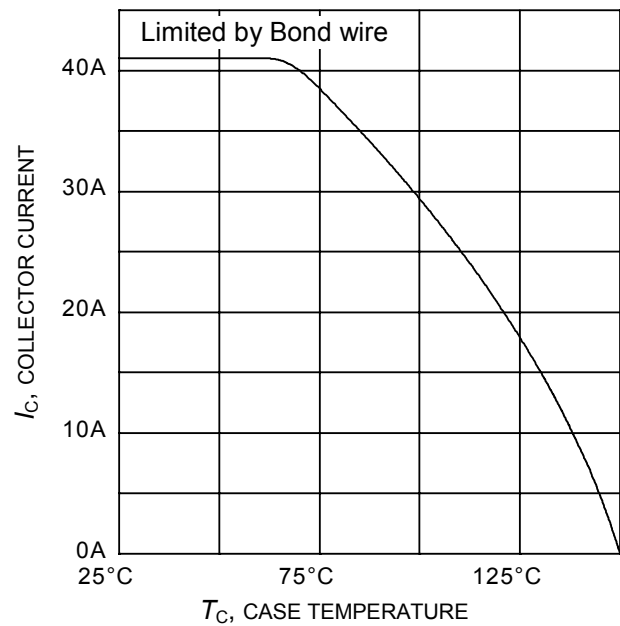


Figure 4. Collector current as a function of case temperature
 ($V_{GE} \leq 15\text{V}$, $T_j \leq 150^\circ\text{C}$)

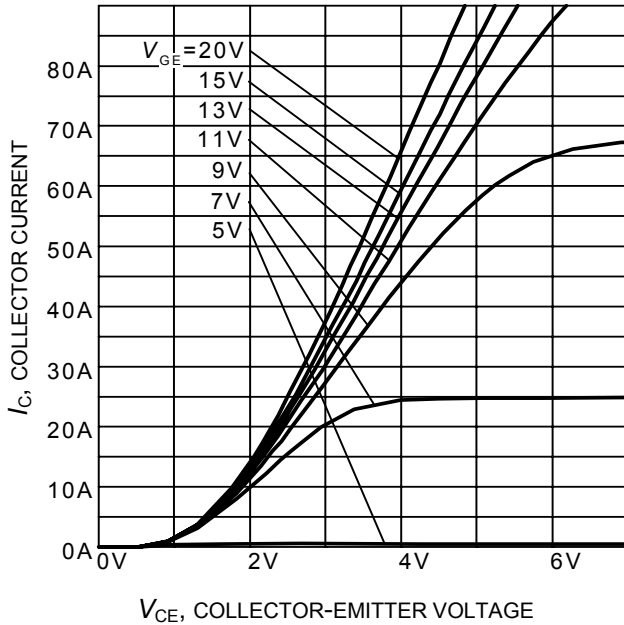


Figure 5. Typical output characteristic
($T_j = 25^\circ\text{C}$)

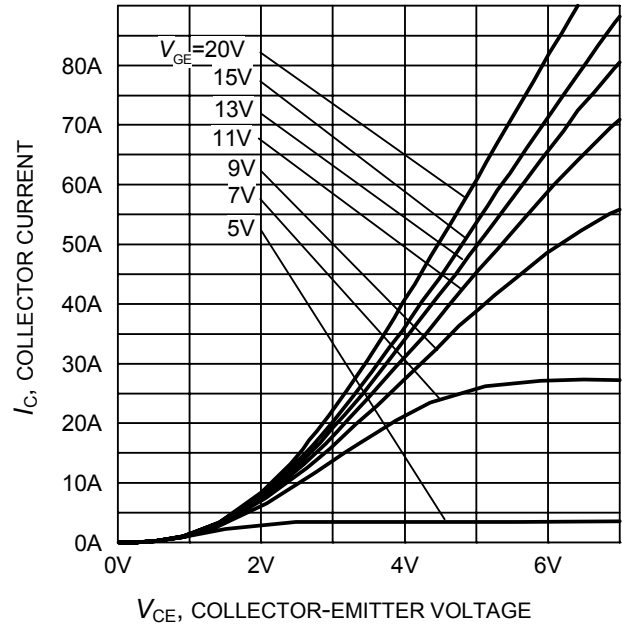


Figure 6. Typical output characteristic
($T_j = 150^\circ\text{C}$)

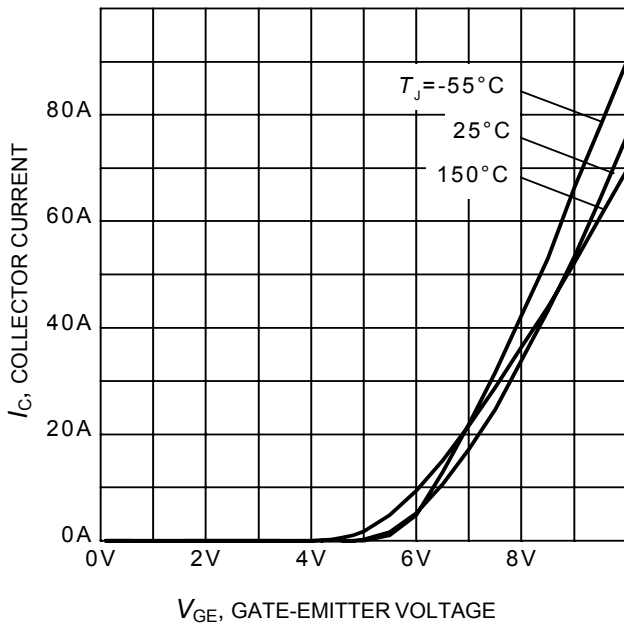


Figure 7. Typical transfer characteristic
($V_{CE} = 10\text{V}$)

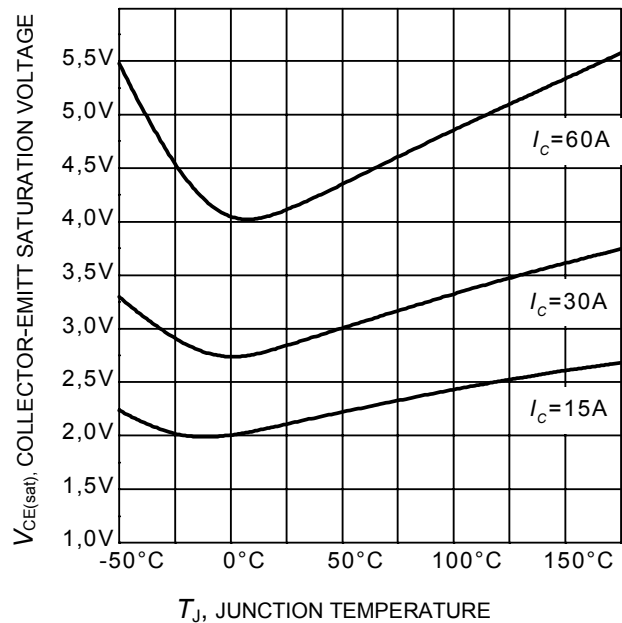


Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature
($V_{GE} = 15\text{V}$)

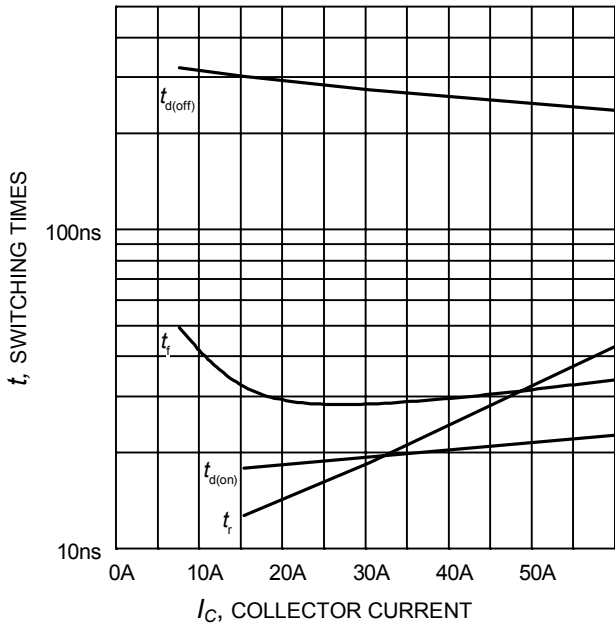


Figure 9. Typical switching times as a function of collector current
(inductive load, $T_J=150^{\circ}\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=0/15\text{V}$, $R_G=11\Omega$, Dynamic test circuit in Figure E)

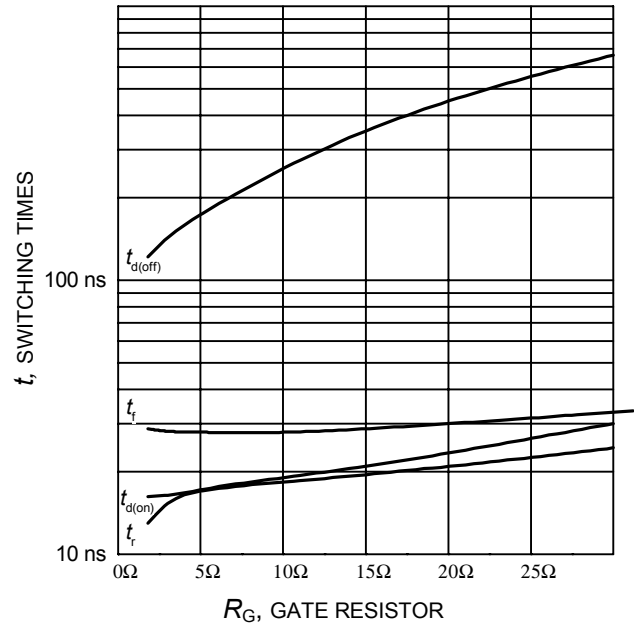


Figure 10. Typical switching times as a function of gate resistor
(inductive load, $T_J=150^{\circ}\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=0/15\text{V}$, $I_C=30\text{A}$, Dynamic test circuit in Figure E)

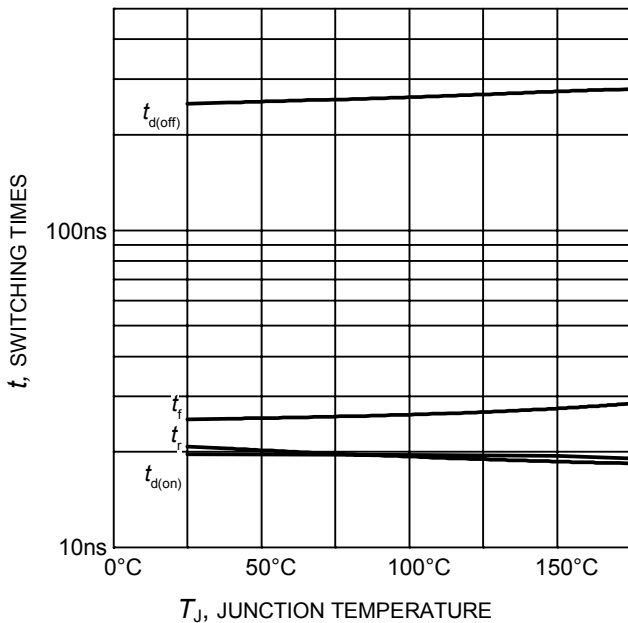


Figure 11. Typical switching times as a function of junction temperature
(inductive load, $V_{CE}=400\text{V}$, $V_{GE}=0/15\text{V}$, $I_C=30\text{A}$, $R_G=11\Omega$, Dynamic test circuit in Figure E)

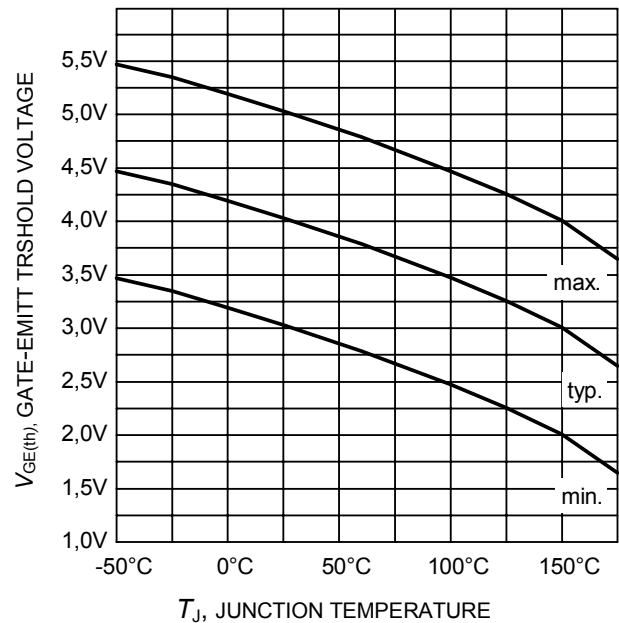


Figure 12. Gate-emitter threshold voltage as a function of junction temperature
($I_C = 0.7\text{mA}$)

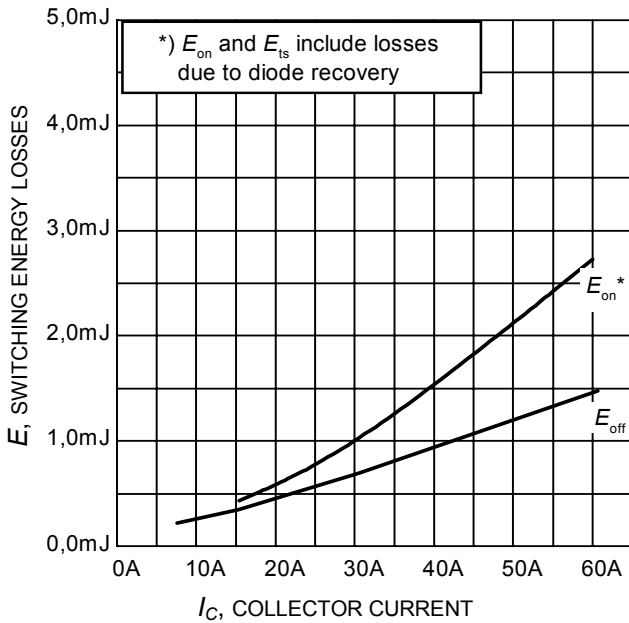


Figure 13. Typical switching energy losses as a function of collector current
(inductive load, $T_J=150^\circ\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=0/15\text{V}$, $R_G=11\Omega$, Dynamic test circuit in Figure E)

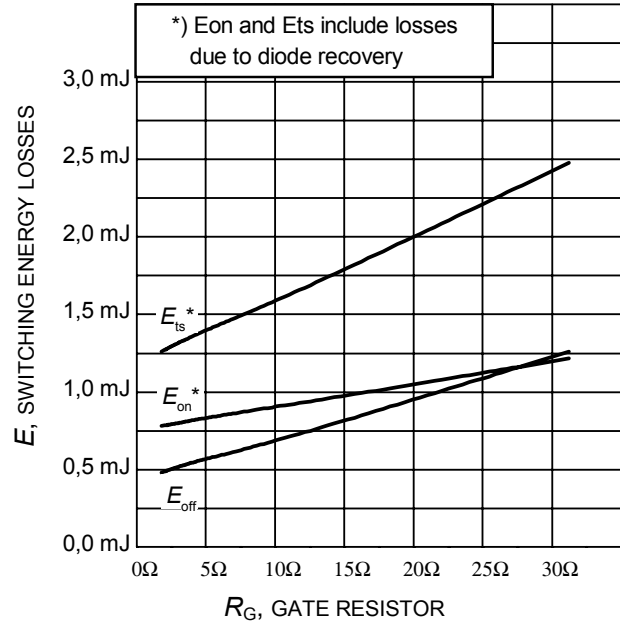


Figure 14. Typical switching energy losses as a function of gate resistor
(inductive load, $T_J=150^\circ\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=0/15\text{V}$, $I_C=30\text{A}$, Dynamic test circuit in Figure E)

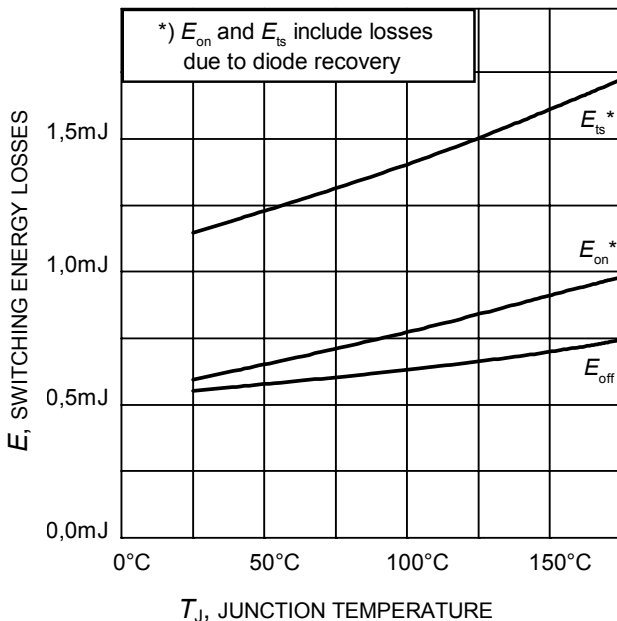


Figure 15. Typical switching energy losses as a function of junction temperature
(inductive load, $V_{CE}=400\text{V}$, $V_{GE}=0/15\text{V}$, $I_C=30\text{A}$, $R_G=11\Omega$, Dynamic test circuit in Figure E)

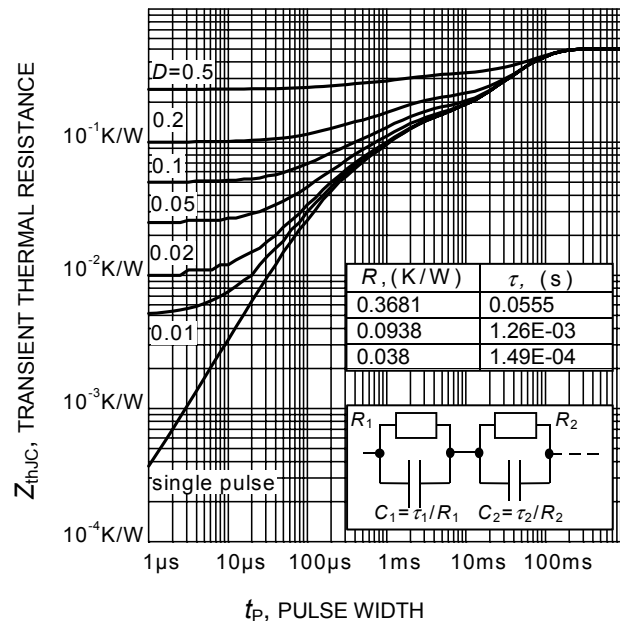


Figure 16. IGBT transient thermal resistance
($D = t_p / T$)

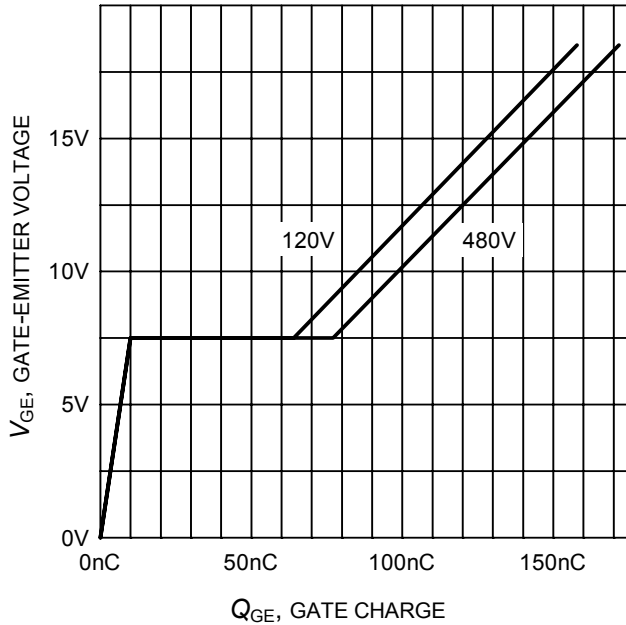


Figure 17. Typical gate charge
($I_C=30\text{ A}$)

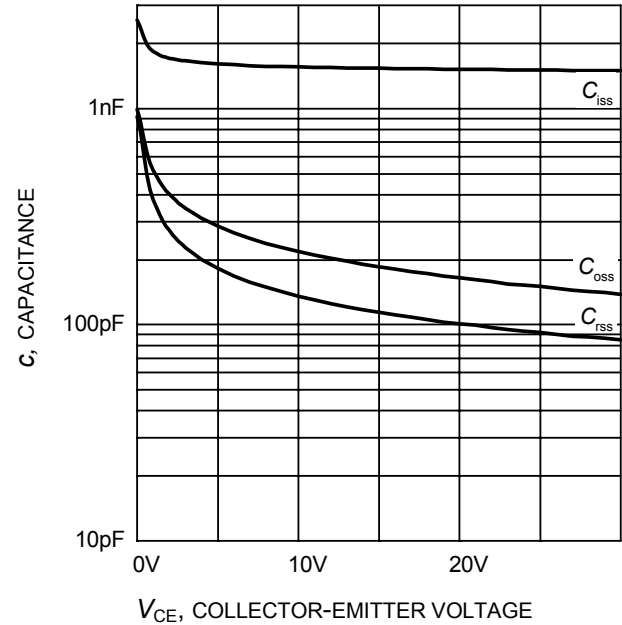


Figure 18. Typical capacitance as a function of collector-emitter voltage
($V_{GE}=0\text{V}$, $f = 1\text{ MHz}$)

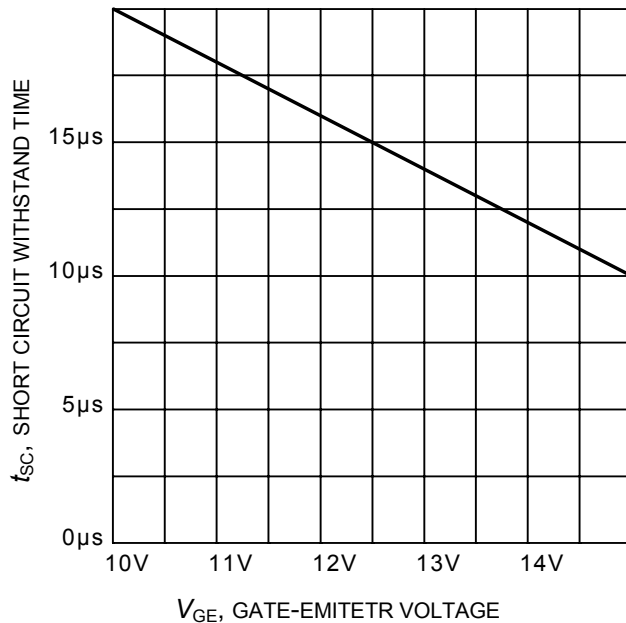


Figure 19. Short circuit withstand time as a function of gate-emitter voltage
($V_{CE}=600\text{V}$, start at $T_J=25^\circ\text{C}$)

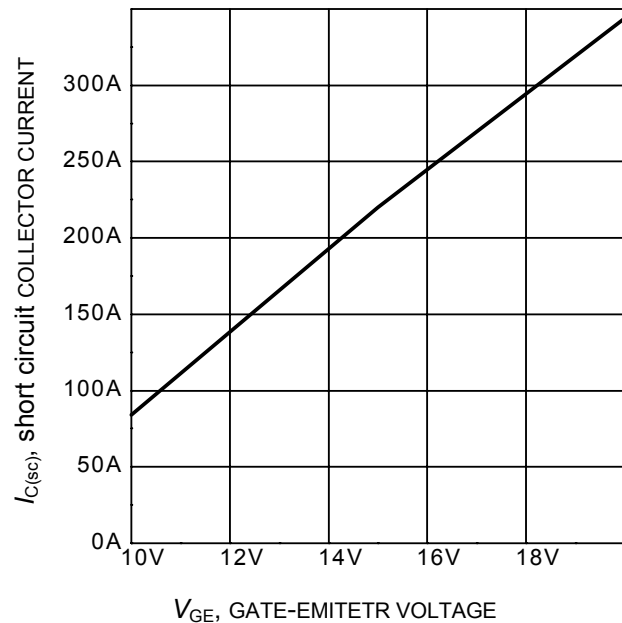
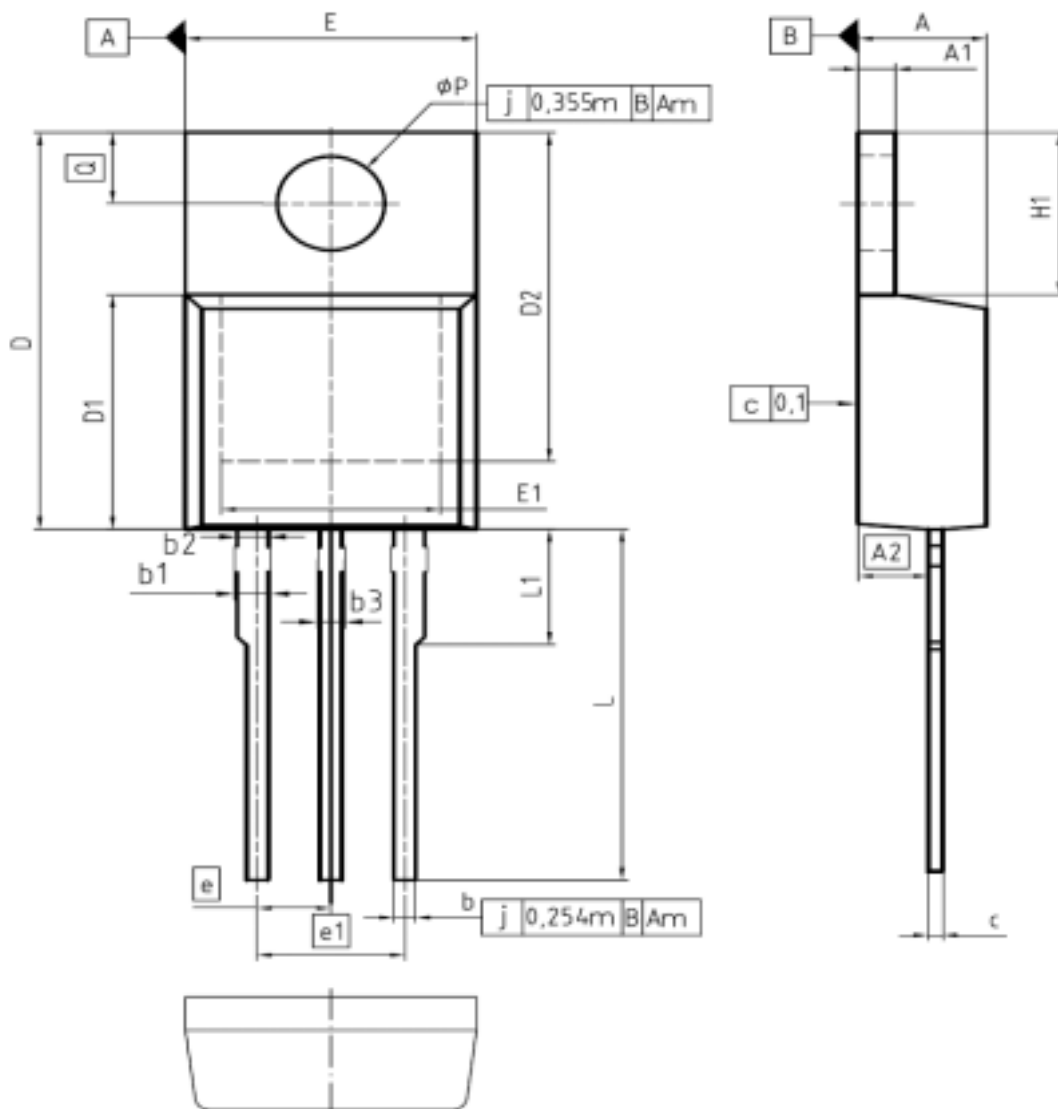


Figure 20. Typical short circuit collector current as a function of gate-emitter voltage
($V_{CE} \leq 600\text{V}$, $T_J \leq 150^\circ\text{C}$)

PG-TO220-3-1



| DIM | MILLIMETERS | | INCHES | |
|----------|-------------|-------|--------|-------|
| | MIN | MAX | MIN | MAX |
| A | 4.30 | 4.57 | 0.169 | 0.180 |
| A1 | 1.17 | 1.40 | 0.046 | 0.055 |
| A2 | 2.15 | 2.72 | 0.085 | 0.107 |
| b | 0.65 | 0.86 | 0.026 | 0.034 |
| b1 | 0.95 | 1.40 | 0.037 | 0.055 |
| b2 | 0.95 | 1.15 | 0.037 | 0.045 |
| b3 | 0.65 | 1.15 | 0.026 | 0.045 |
| c | 0.33 | 0.60 | 0.013 | 0.024 |
| D | 14.81 | 15.95 | 0.583 | 0.628 |
| D1 | 8.51 | 9.45 | 0.335 | 0.372 |
| D2 | 12.19 | 13.10 | 0.480 | 0.516 |
| E | 9.70 | 10.36 | 0.382 | 0.408 |
| E1 | 6.50 | 8.60 | 0.256 | 0.339 |
| e | 2.54 | | 0.100 | |
| e1 | 5.08 | | 0.200 | |
| N | 3 | | 3 | |
| H1 | 5.90 | 6.90 | 0.232 | 0.272 |
| L | 13.00 | 14.00 | 0.512 | 0.551 |
| L1 | - | 4.80 | - | 0.189 |
| ϕP | 3.60 | 3.89 | 0.142 | 0.153 |
| Q | 2.60 | 3.00 | 0.102 | 0.118 |

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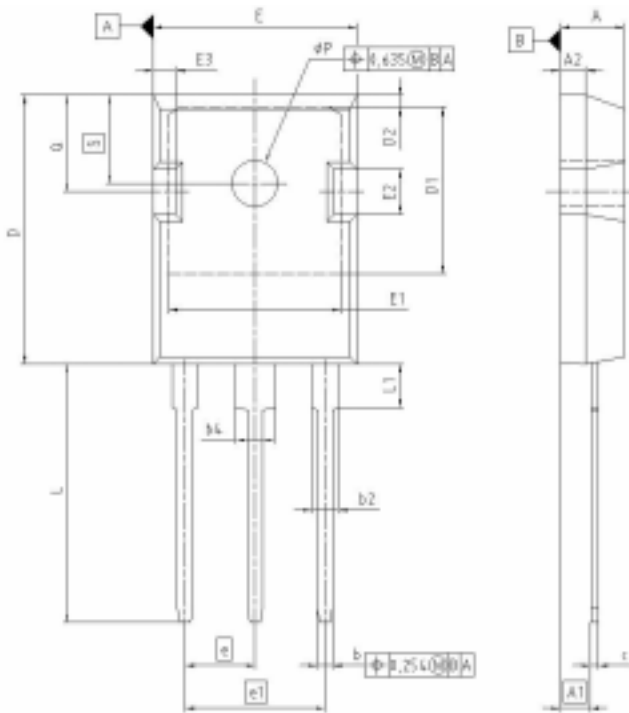
SCALE

EUROPEAN PROJECTION

ISSUE DATE
23-08-2007

REVISION
05

PG-TO247-3-21



| DIM | MILLIMETERS | | INCHES | |
|----------|-------------|--------|--------|-------|
| | MIN | MAX | MIN | MAX |
| A | 4.900 | 5.157 | 0.193 | 0.203 |
| A1 | 2.275 | 2.527 | 0.090 | 0.100 |
| A2 | 1.653 | 2.107 | 0.075 | 0.083 |
| b | 1.073 | 1.327 | 0.042 | 0.052 |
| b2 | 1.903 | 2.388 | 0.075 | 0.094 |
| b4 | 2.870 | 3.454 | 0.113 | 0.136 |
| c | 0.549 | 0.752 | 0.021 | 0.030 |
| D | 20.823 | 21.077 | 0.820 | 0.830 |
| D1 | 17.323 | 17.831 | 0.682 | 0.702 |
| D2 | 1.063 | 1.317 | 0.042 | 0.052 |
| E | 15.773 | 16.027 | 0.621 | 0.631 |
| E1 | 13.893 | 14.147 | 0.547 | 0.557 |
| E2 | 3.683 | 3.057 | 0.145 | 0.155 |
| E3 | 1.803 | 1.907 | 0.070 | 0.076 |
| e | 5.450 | | 0.215 | |
| e1 | 10.900 | | 0.430 | |
| N | 3 | | 3 | |
| L | 20.953 | 20.307 | 0.799 | 0.799 |
| L1 | 4.166 | 4.472 | 0.164 | 0.175 |
| ϕP | 3.259 | 3.261 | 0.128 | 0.128 |
| Q | 5.405 | 5.747 | 0.213 | 0.226 |
| S | 6.043 | 6.297 | 0.238 | 0.248 |

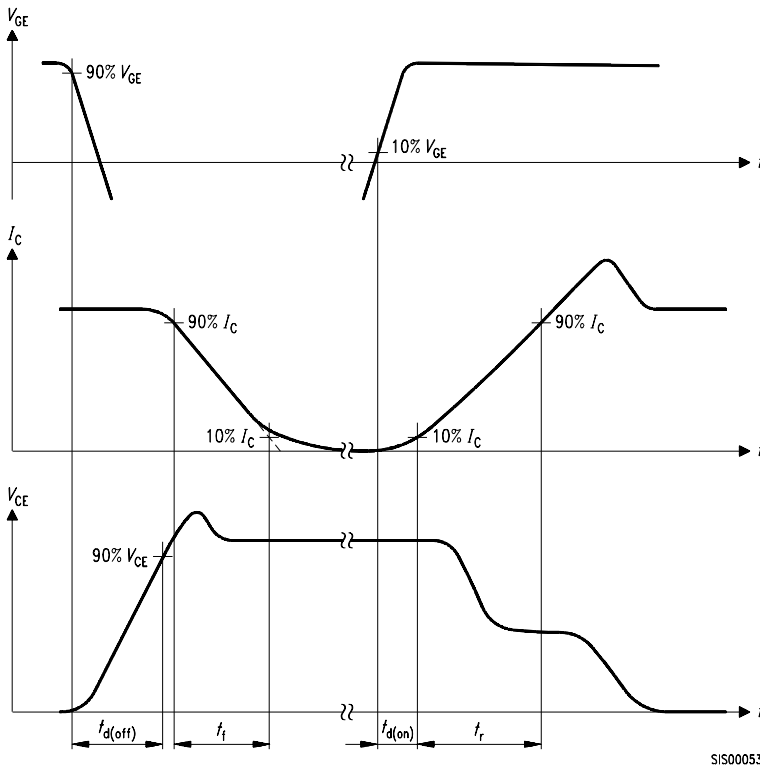


Figure A. Definition of switching times

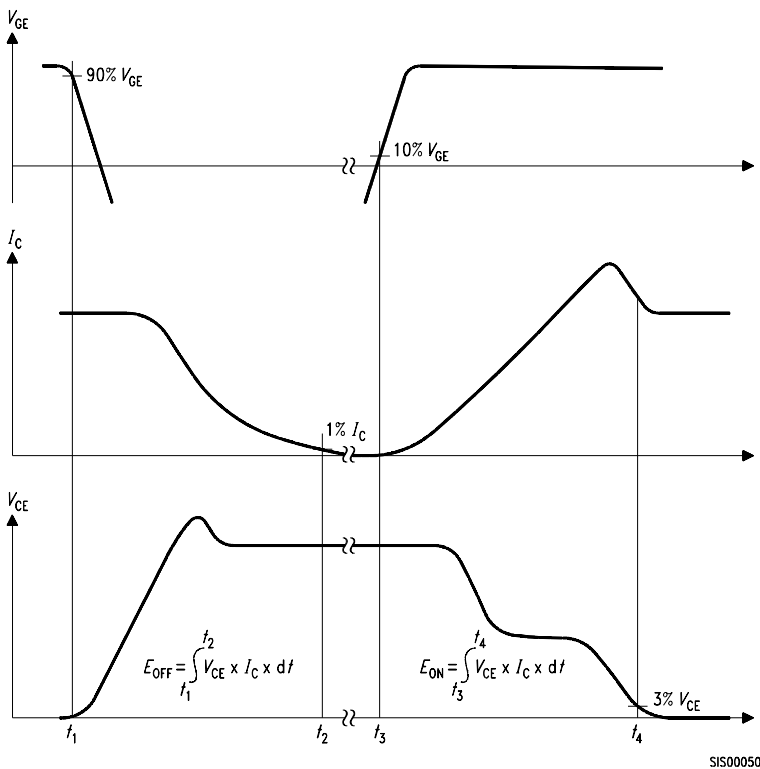


Figure B. Definition of switching losses

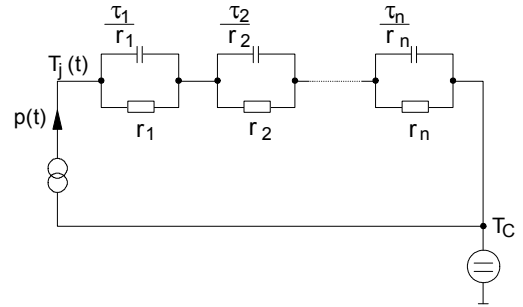


Figure D. Thermal equivalent circuit

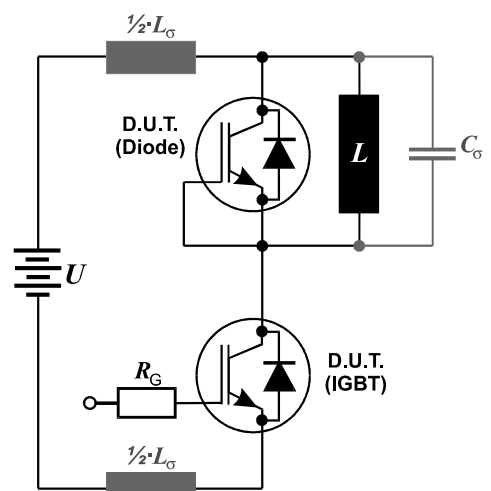


Figure E. Dynamic test circuit
Leakage inductance $L_{\sigma} = 60\text{nH}$
and Stray capacity $C_{\sigma} = 40\text{pF}$.

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